

Modelithics News - September 2010

What designers are saying:

"The Modelithics Libraries allow us to achieve first-pass Success for GHz designs on printed circuit boards."

Justin Magers, National Instruments

"I have been very pleased with the results I'm getting with the Modelithics CLR Library for Genesys. The agreement that I observe with measured results is the best I've ever achieved. By using these libraries as part of my design flow, more can be accomplished with less time and lower (BOM) material costs, period."

Lance Lascari of RFDude.com, LLC



Modelithics Significantly Expands Its Scalable Passive Model Library for Agilent

Genesys



Agilent Technologies

Modelithics™ latest model library release for Agilent Technologies' Genesys encompasses all of our latest models and sub-library version into single installer-providing increased efficiency and flexibility. Find out more about Modelithics CLR Library v7.3 below. .

[Press Release](#) [Release Notes](#)

LINC Power Amplifiers for Reducing Out-of-Band Spectral Re-Growth: A Comparative Study:

This comparative study by Baylor University was conducted using the Modelithics Libraries and presented at WAMICON 2010. [Read the study now.](#)

Solutions for RF Board and Module Designers

This white paper discusses how superior models can accelerate product schedules, reducing development, manufacturing and support costs. Read more about how accurate models can yield an extremely high return on investment because they prevent design problems at the very earliest, least costly stage. [Solutions](#)

Interested in High Power GaN Models?

The success of simulation-based design of power amplifiers for wireless communications depends on the accuracy of nonlinear models that are used to represent the transistors. With AlGaIn/GaN HEMT modeling, much work has been done to advance models on several fronts. With the powerful benefits of GaN devices come unique challenges encountered due to trapping effects, related current collapse effects, the high voltage and currents involved thermal and other challenges.

An article entitled "Modeling GaN: Powerful but Challenging!:" appears in the October issue of the *IEEE Microwave Magazine*. The paper reviews various modeling approaches and discusses considerations for successful measurement-based modeling of GaN transistors using various HEMT models available for popular microwave non-linear circuit simulators. Examples are shown for accurate GaN models developed by Modelithics using EEHEMT, CFET and Angelov modeling templates. The article is co-authored by Modelithics co-founder Larry Dunleavy along with Charles Baylis, Walter Curtice and Rick Connick.

For more information and sample models visit:

<http://www.Modelithics.com>

Precision Measurements and Models You Trust